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**SIMULATION AND MODELING OF TUNNELING CARBON
NANOTUBES FIELD EFFECT TRANSISTORS (T-CNFETs)**

By

Mohamed Nabil Mohamed Mostafa El-Zeftawi

B.Sc. in Electronics and Communications Engineering – Cairo University

A Thesis Submitted to the
Faculty of Engineering at Cairo University
in Partial Fulfillment of the
Requirements for the Degree of
Master of Science
in
Engineering Physics

Faculty of Engineering, Cairo University
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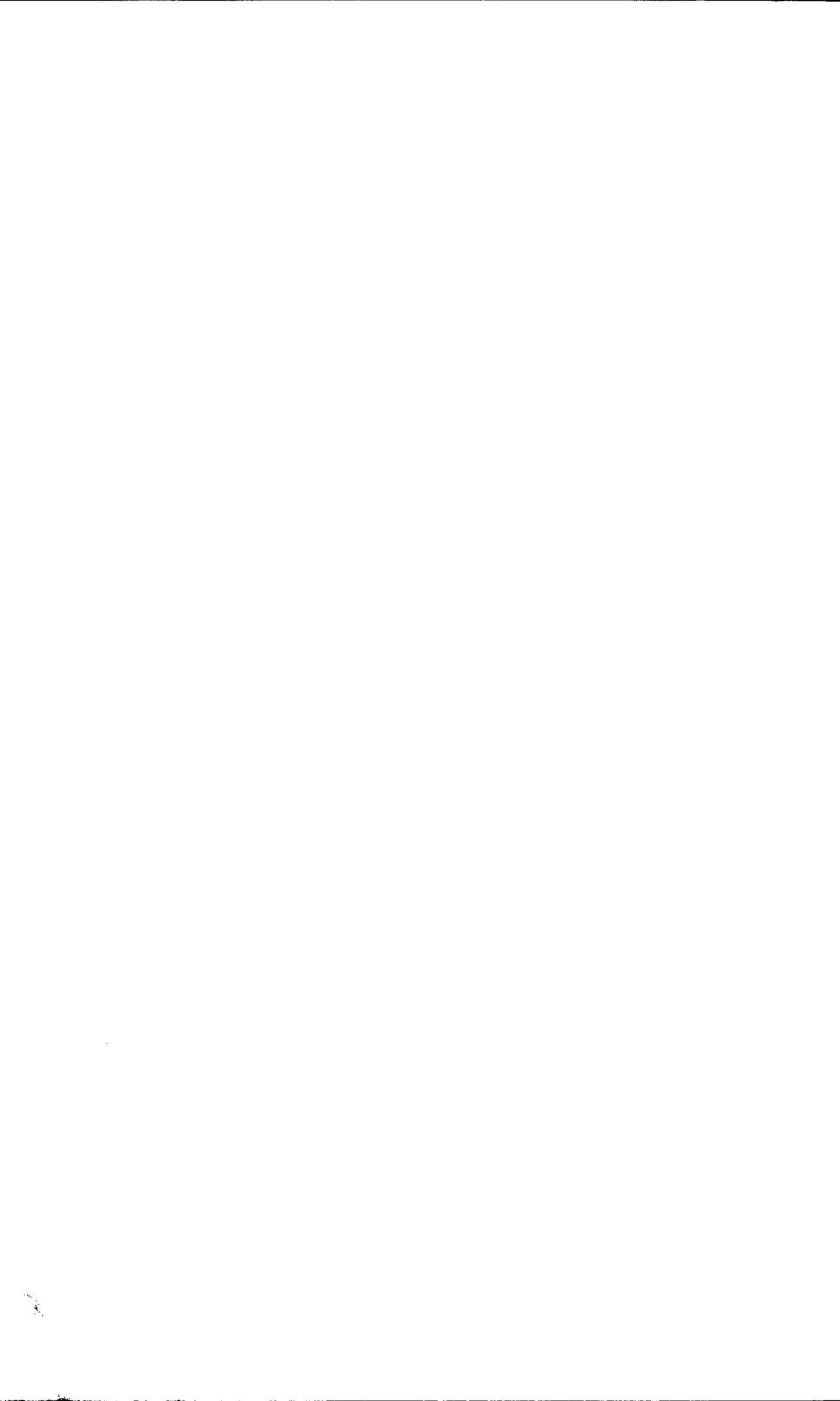
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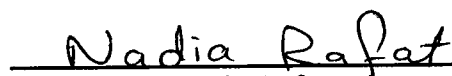
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